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November 2013

FQP10N20C / FQPF10N20C N-Channel QFET[®] MOSFET 200 V, 9.5 A, 360 mΩ

Features

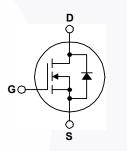
- + 9.5 A, 200 V, $R_{DS(on)}$ = 360 m Ω (Max.) @ V_{GS} = 10 V, I_{D} = 4.75 A
- Low Gate Charge (Typ. 20 nC)
- Low Crss (Typ. 40.5 pF)
- 100% Avalanche Tested

Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.







MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter		FQP10N20C	FQPF10N20C	Unit
V _{DSS}	Drain to Source Voltage		200		V	
I _D	Decis Coment	-Continuous (T _C = 25 ^o C)		9.5	9.5 *	А
	Drain Current	-Continuous (T _C = 100 ^o C)		6.0	6.0 *	А
lом	Drain Current	- Pulsed	(Note 1)	38	38 *	А
V _{GSS}	Gate to Source Voltage		± 30		V	
E _{AS}	Single Pulsed Avalanche Energy		(Note 2)	210		mJ
AR	Avalanche Current		(Note 1)	9.5		А
AR	Repetitive Avalanche Energy		(Note 1)	7.2		mJ
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	5.5		V/ns
P _D	Dewen Dissinction	(T _C = 25 ^o C)		72	38	W
	Power Dissipation	- Derate above 25°C		0.57	0.3	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150		°C	
TL	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds			300		°C

*Drain current limited by maximum junction temperature

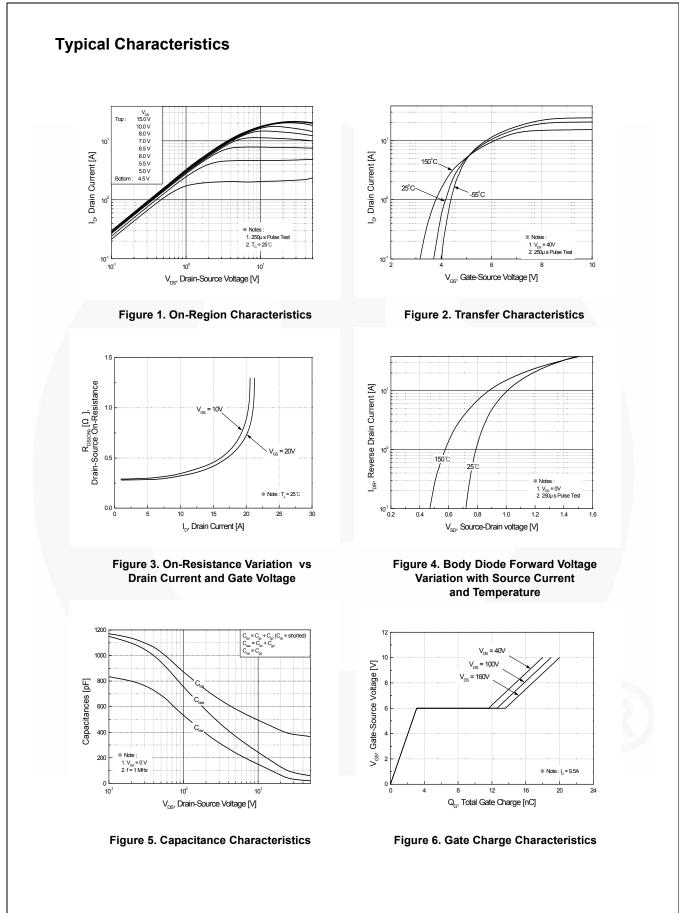
Thermal Characteristics

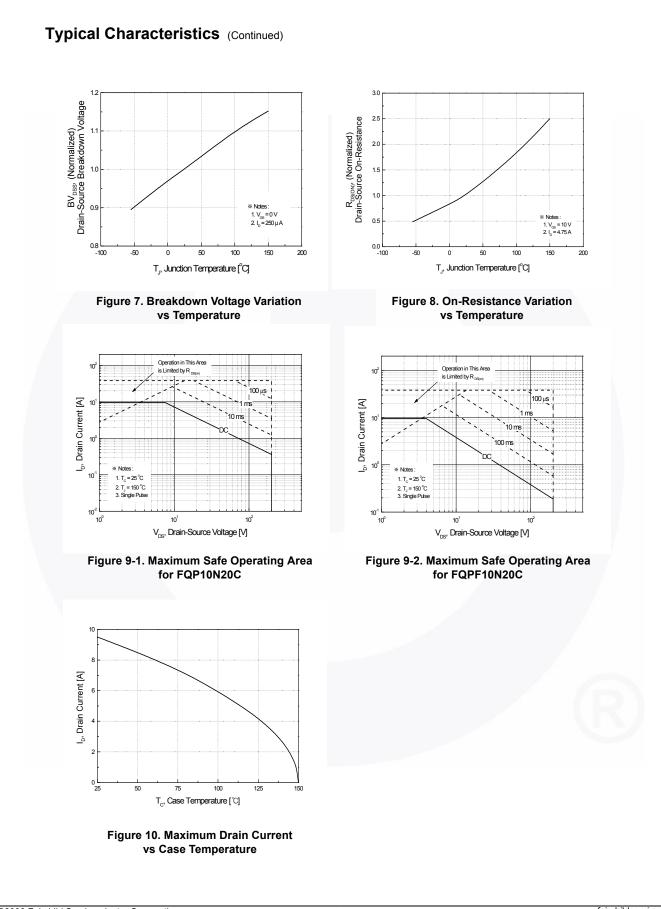
Symbol	Parameter	FQP10N20C	FQPF10N20C	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	1.74	3.33	°C/W
R_{\thetaJA}	Thermal Resistance, Junction to Ambient, Max	62.5	62.5	°C/W

	vice Marking	Device	Package	Reel Size	Tape Width	QL	antity
FC	QP10N20C	FQP10N20C	TO-220	Tube	N/A	50) units
FQPF10N20C FQPF10N20C		TO-220F	Tube	N/A	50	50 units	
Electri	cal Characte	eristics T _C = 25°C u	nless otherwise noted				
Symbol			Test Conditions		Тур	Max	Unit
Off Cha	aracteristics						
BV _{DSS}	T	eakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	200			V
ΔBV_{DSS}		-					v
$/ \Delta T_{J}$	cient	age Temperature Coeffi-	$I_D = 250 \ \mu A$, Referenced to 25	5°C	0.28		V/°C
I _{DSS} Zero Gat	Zero Gate Voltag	ne Drain Current	V_{DS} = 200 V, V_{GS} = 0 V			10	μA
			V _{DS} = 160 V, T _C = 125°C			100	μA
I _{GSSF}	Gate-Body Leakage Current, Forward		V_{GS} = 30 V, V_{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse		V_{GS} = -30 V, V_{DS} = 0 V			-100	nA
On Cha	aracteristics						
V _{GS(th)}	Gate Threshold	Voltage	V_{DS} = V_{GS} , I_D = 250 μ A	2.0		4.0	V
R _{DS(on)}	Static Drain-Sou On-Resistance	rce	V _{GS} = 10 V, I _D = 4.75 A		0.29	0.36	Ω
9 _{FS}	Forward Transco	onductance	V _{DS} = 40 V, I _D = 4.75 A		5.5		S
Dynam C _{iss} C _{oss} C _{rss}	ic Characteris	nce	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz		395 97 40.5	510 125 53	pF pF
	ing Characteri						
t _{d(on)}	Turn-On Delay T		V_{DD} = 100 V, I _D = 9.5 A, R _G = 25 Ω		11	30	ns
t _r	Turn-On Rise Tir				92	190	ns
t _{d(off)}	Turn-Off Delay T		-	(Note 4)	70	150	ns
t _f	Turn-Off Fall Tim				72	160	ns
0	Total Gate Charg		$V_{DS} = 160 \text{ V}, \text{ I}_{D} = 9.5 \text{ A},$		20	26	nC
	Coto Course Ol		$V_{\rm GS} = 10 \text{ V}$		3.1		nC
Q _{gs}	Gate-Source Cha	0		(Nicto 4)	10 5		
Q _g Q _{gs} Q _{gd}	Gate-Source Cha Gate-Drain Char	0		(Note 4)	10.5		nC
ସୁ _{gs} ସୁ _{gd}	Gate-Drain Char	ge		(Note 4)	10.5		
ଦ୍ର _{gs} ଦୁ _{gd} Drain-S	Gate-Drain Char	ge	I Maximum Ratings	(Note 4)		9.5	A
ସ୍ _{gs} ସୁ _{gd} Drain-S s SM	Gate-Drain Char Source Diode (Maximum Contir Maximum Pulsed	ge Characteristics and nuous Drain-Source Diode d Drain-Source Diode Fo	I Maximum Ratings e Forward Current ward Current	(Note 4)		9.5 38	<u>,</u>
Q _{gs} Q _{gd} Drain-S Is Is V _{SD}	Gate-Drain Char Source Diode (Maximum Contir Maximum Pulsed	ge Characteristics and nuous Drain-Source Diode	I Maximum Ratings e Forward Current ward Current $V_{GS} = 0 V, I_S = 9.5 A$				A
Q _{gs} Q _{gd} Drain-S	Gate-Drain Char Source Diode (Maximum Contir Maximum Pulsed	ge Characteristics and nuous Drain-Source Diode d Drain-Source Diode For ode Forward Voltage	I Maximum Ratings e Forward Current ward Current			38	AAA

4. Essentially independent of operating temperature.

FQP10N20C / FQPF10N20C — N-Channel QFET® MOSFET





Typical Characteristics (Continued)

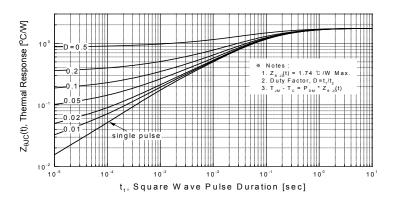
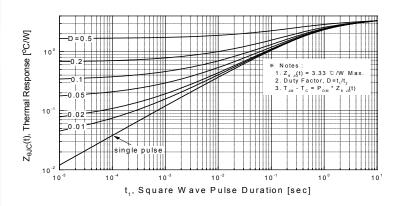
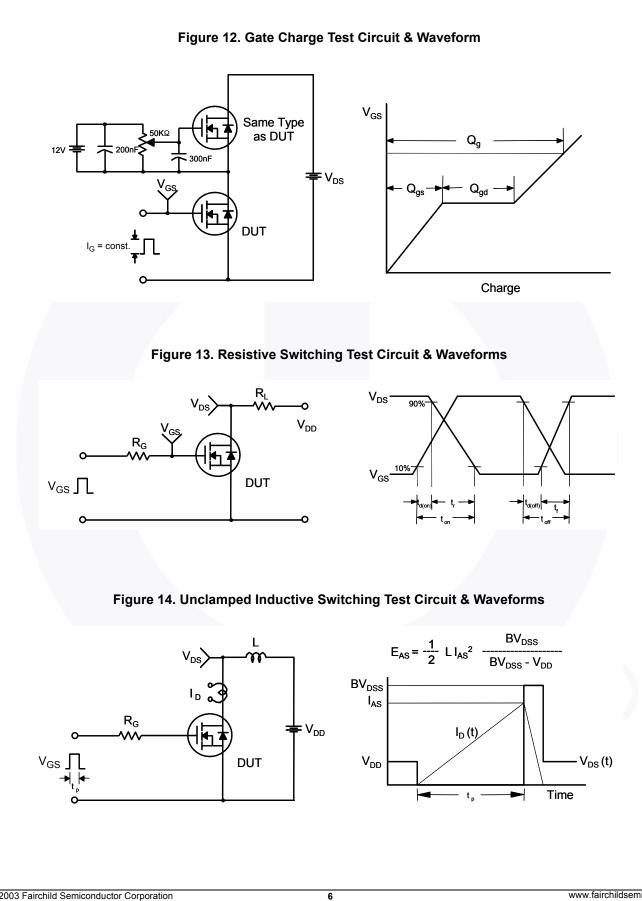


Figure 11-1. Transient Thermal Response Curve for FQP10N20C

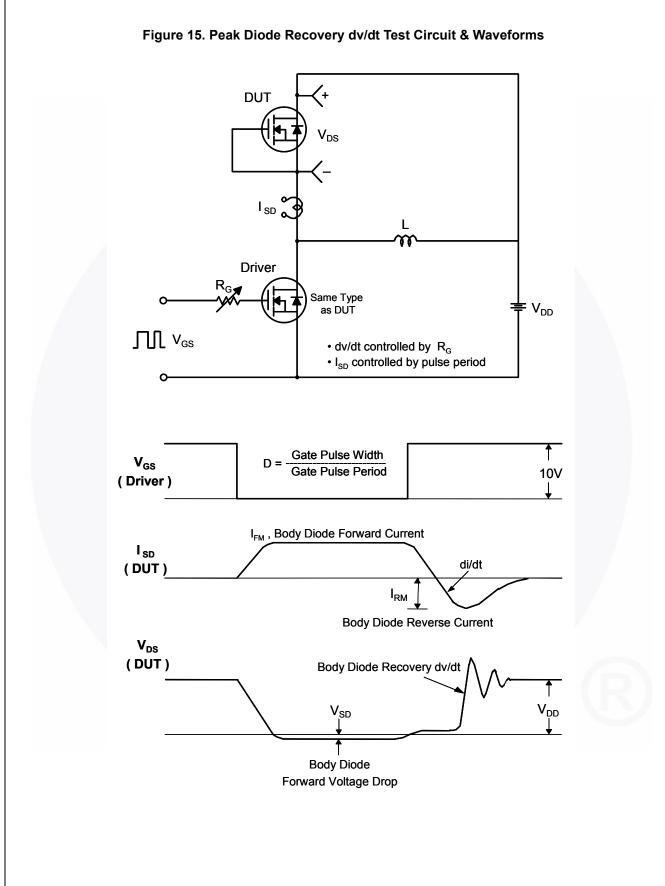


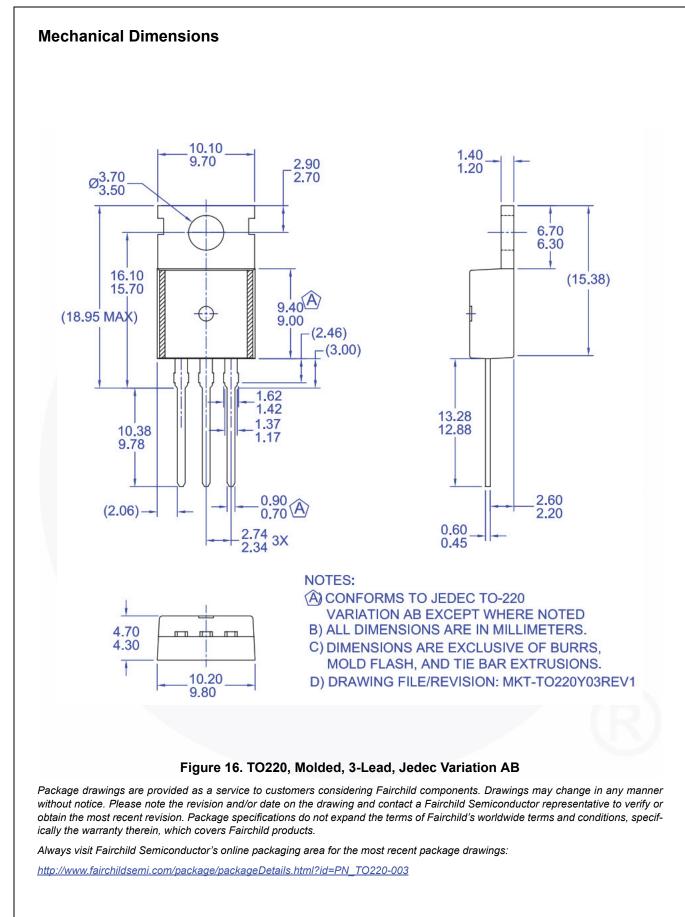


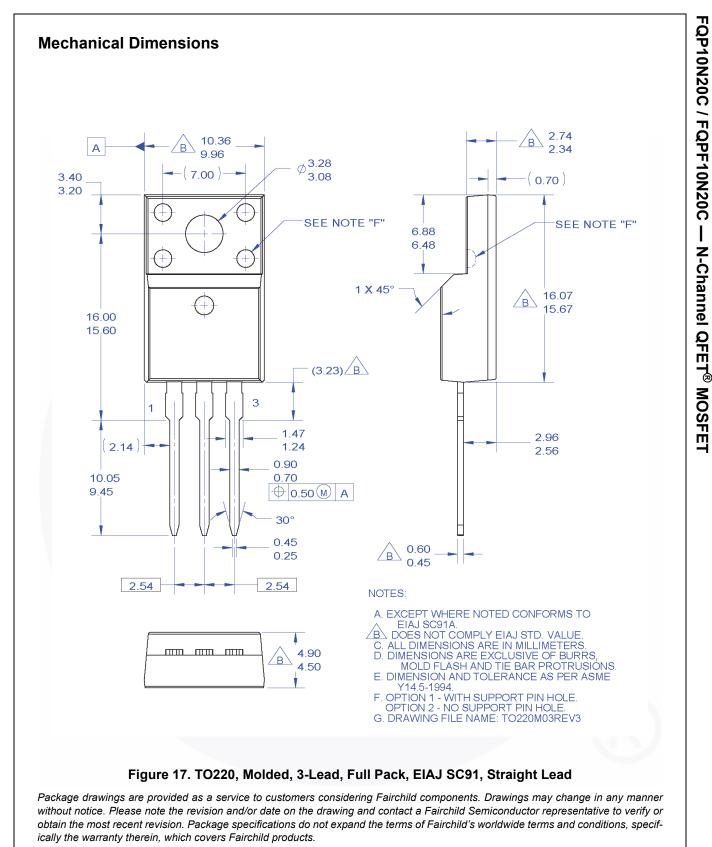


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